

**TOSHIBA****1SS321**

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

**1SS321**

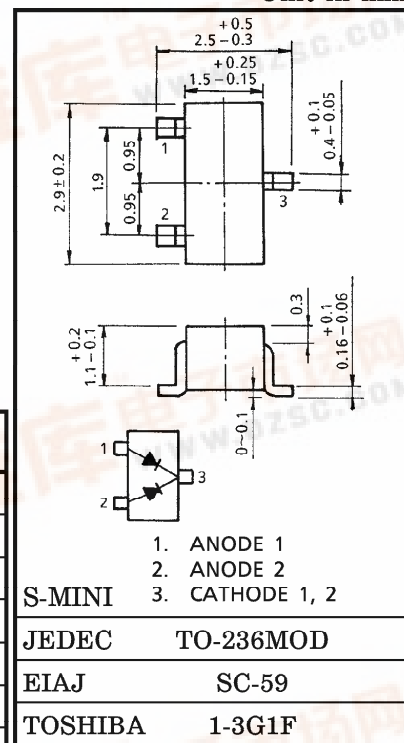
LOW VOLTAGE HIGH SPEED SWITCHING.

Unit in mm

- Low Forward Voltage :  $V_F = 0.42V$  (Typ.)
- Low Reverse Current :  $I_R = 500nA$  (Max.)
- Small Package : SC-59 (SOT-23MOD)

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	$V_{RM}$	12	V
Reverse Voltage	$V_R$	10	V
Maximum (Peak) Forward Current	$I_{FM}$	150 (*)	mA
Average Forward Current	$I_O$	50 (*)	mA
Surge Current ( $t=10ms$ )	$I_{FSM}$	1000 (*)	mA
Power Dissipation	P	150	mW
Junction Temperature	$T_j$	125	$^\circ C$
Storage Temperature Range	$T_{stg}$	$-55 \sim 125$	$^\circ C$

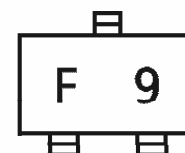


Weight : 0.012g

(\*) Unit Rating. Total Rating=Unit Rating $\times$ 1.5.ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F = 1mA$	—	0.32	—	V
	$V_F(2)$	$I_F = 10mA$	—	0.42	—	
	$V_F(3)$	$I_F = 50mA$	—	0.63	1.00	
Reverse Current	$I_R$	$V_R = 10V$	—	—	500	nA
Total Capacitance	$C_T$	$V_R = 0, f = 1MHz$	—	3.2	4.5	pF

MARKING



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